

Single Switch IGBT Module

PDS5615-4.1 January 2009(LN26570)

FEATURES

- Soft Punch Through Silicon
- Isolated AISiC Base with AlN Substrates
- High Thermal Cycling Capability
- 10µs Short Circuit Withstand
- Lead Free construction

APPLICATIONS

- High Reliability Inverters
- Motor Controllers
- Traction Drives
- Choppers

The Powerline range of high power modules includes half bridge, chopper, dual, single and bi-directional switch configurations covering voltages from 1200V to 6500V and currents up to 3600A.

The DIM800NSM33-F000 is a single switch 3300V, soft punch through n-channel enhancement mode, insulated gate bipolar transistor (IGBT) module. The IGBT has a wide reverse bias safe operating area (RBSOA) plus 10us short circuit withstand. This device is optimised for traction drives and other applications requiring high thermal cycling capability.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

DIM800NSM33-F000

Note: When ordering, please use the complete part number

KEY PARAMETERS

V_{CES}		3300V
$V_{CE(sat)}$ *	(typ)	2.8V
I_C	(max)	800A
$I_{C(PK)}$	(max)	1600A

*(measured at the auxiliary terminals)

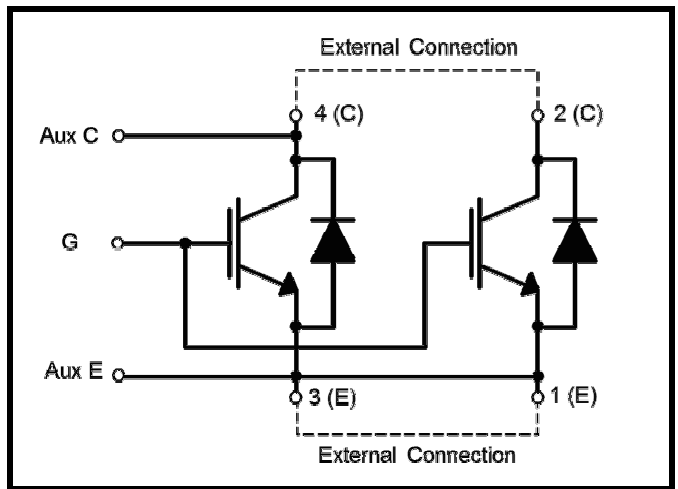


Fig. 1 Circuit configuration



Fig. 2 Package

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

$T_{\text{case}} = 25^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V_{CES}	Collector-emitter voltage	$V_{\text{GE}} = 0\text{V}$	3300	V
V_{GES}	Gate-emitter voltage		± 20	V
I_{C}	Continuous collector current	$T_{\text{case}} = 90^{\circ}\text{C}$	800	A
$I_{\text{C(PK)}}$	Peak collector current	1ms, $T_{\text{case}} = 115^{\circ}\text{C}$	1600	A
P_{max}	Max. transistor power dissipation	$T_{\text{case}} = 25^{\circ}\text{C}$, $T_{\text{j}} = 150^{\circ}\text{C}$	10.4	kW
I^2t	Diode I^2t value	$V_{\text{R}} = 0\text{V}$, $t_{\text{p}} = 10\text{ms}$, $T_{\text{j}} = 125^{\circ}\text{C}$	320	kA^2s
V_{isol}	Isolation voltage	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	6	kV
Q_{PD}	Partial discharge	IEC1287. $V_1 = 3500\text{V}$, $V_2 = 2600\text{V}$, 50Hz RMS	10	pC

THERMAL AND MECHANICAL RATINGS

Internal insulation material: AlN
 Baseplate material: AlSiC
 Creepage distance: 33mm
 Clearance: 20mm
 CTI (Critical Tracking Index): 350

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$R_{\text{th(j-c)}}$	Thermal resistance - transistor	Continuous dissipation - junction to case			12	$^{\circ}\text{C}/\text{kW}$
$R_{\text{th(j-c)}}$	Thermal resistance - diode	Continuous dissipation - junction to case			24	$^{\circ}\text{C}/\text{kW}$
$R_{\text{th(c-h)}}$	Thermal resistance - case to heatsink	Mounting torque 5Nm (with mounting grease)			8	$^{\circ}\text{C}/\text{kW}$
T_{j}	Junction temperature	Transistor			150	$^{\circ}\text{C}$
		Diode			125	$^{\circ}\text{C}$
T_{stg}	Storage temperature range		-40		125	$^{\circ}\text{C}$
	Screw torque	Mounting M6			5	Nm
		Electrical connections – M4			2	Nm
		Electrical connections – M8			10	Nm

ELECTRICAL CHARACTERISTICS
 $T_{case} = 25^{\circ}C$ unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units	
I_{CES}	Collector cut-off current	$V_{GE} = 0V, V_{CE} = V_{CES}$			4	mA	
		$V_{GE} = 0V, V_{CE} = V_{CES}, T_{case} = 125^{\circ}C$			60	mA	
I_{GES}	Gate leakage current	$V_{GE} = \pm 15V, V_{CE} = 0V$			1	μA	
$V_{GE(TH)}$	Gate threshold voltage	$I_C = 80mA, V_{GE} = V_{CE}$	5.5	6.5	7.0	V	
$V_{CE(sat)}^{\dagger}$	Collector-emitter saturation voltage	$V_{GE} = 15V, I_C = 800A$		2.8		V	
		$V_{GE} = 15V, I_C = 800A, T_J = 125^{\circ}C$		3.6		V	
I_F	Diode forward current	DC		800		A	
I_{FM}	Diode maximum forward current	$t_p = 1ms$		1600		A	
V_F^{\dagger}	Diode forward voltage	$I_F = 800A$		2.9		V	
		$I_F = 800A, T_J = 125^{\circ}C$		3.0		V	
C_{ies}	Input capacitance	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$		144		nF	
C_{res}	Reverse transfer capacitance	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$		2.2		nF	
L_M	Module inductance			15		nH	
R_{INT}	Internal resistance			135		$\mu\Omega$	
SC_{Data}	Short circuit current, I_{SC}	$T_J = 125^{\circ}C, V_{CC} = 2500V$ $V_{GE} \leq 15V, t_p \leq 10\mu s,$ $V_{CE(max)} = V_{CES} - L^* \times di/dt$ IEC 6074-9	I_1		4000		A
			I_2		3700		A

Note:
 \dagger Measured at the auxiliary terminals

 $*$ L is the circuit inductance + L_M

ELECTRICAL CHARACTERISTICS

$T_{case} = 25^{\circ}C$ unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units	
$t_{d(off)}$	Turn-off delay time	$I_C = 800A$ $V_{GE} = \pm 15V$ $V_{CE} = 1800V$ $R_{G(ON)} = 3.9\Omega, R_{G(OFF)} = 6.2\Omega$ $C_{ge} = 220nF, L \sim 100nH$		3.0		μs	
t_f	Fall time			270		ns	
E_{OFF}	Turn-off energy loss				1050		mJ
$t_{d(on)}$	Turn-on delay time				1.3		μs
t_r	Rise time				275		ns
E_{ON}	Turn-on energy loss		$I_C = 800A, V_{GE} = \pm 15V, V_{CE} = 1800V,$ $R_{G(ON)} = 2.7\Omega, C_{ge} = 220nF, L \sim 100nH$		1250		mJ
Q_g	Gate charge			20		μC	
Q_{rr}	Diode reverse recovery charge	$I_F = 800A$ $V_{CE} = 1800V$ $di_F/dt = 4000A/\mu s$		320		μC	
I_{rr}	Diode reverse recovery current			670		A	
E_{rec}	Diode reverse recovery energy				300		mJ

$T_{case} = 125^{\circ}C$ unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units	
$t_{d(off)}$	Turn-off delay time	$I_C = 800A$ $V_{GE} = \pm 15V$ $V_{CE} = 1800V$ $R_{G(ON)} = 3.9\Omega, R_{G(OFF)} = 6.2\Omega$ $C_{ge} = 220nF, L \sim 100nH$		3.1		μs	
t_f	Fall time			280		ns	
E_{OFF}	Turn-off energy loss				1200		mJ
$t_{d(on)}$	Turn-on delay time				1.2		μs
t_r	Rise time				315		ns
E_{ON}	Turn-on energy loss		$I_C = 800A, V_{GE} = \pm 15V, V_{CE} = 1800V,$ $R_{G(ON)} = 2.7\Omega, C_{ge} = 220nF, L \sim 100nH$		1750		mJ
Q_{rr}	Diode reverse recovery charge	$I_F = 800A$ $V_{CE} = 1800V$ $di_F/dt = 4000A/\mu s$		600		μC	
I_{rr}	Diode reverse recovery current			800		A	
E_{rec}	Diode reverse recovery energy				600		mJ

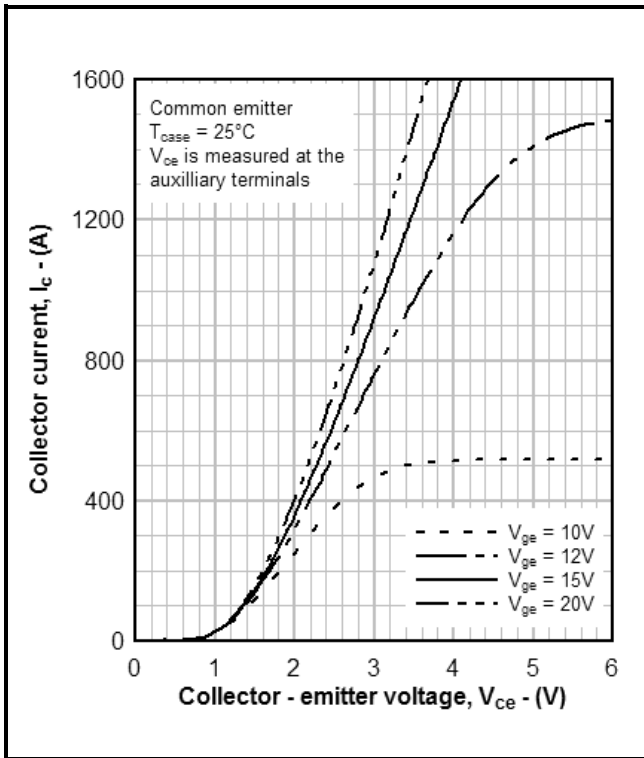


Fig. 3 Typical output characteristics

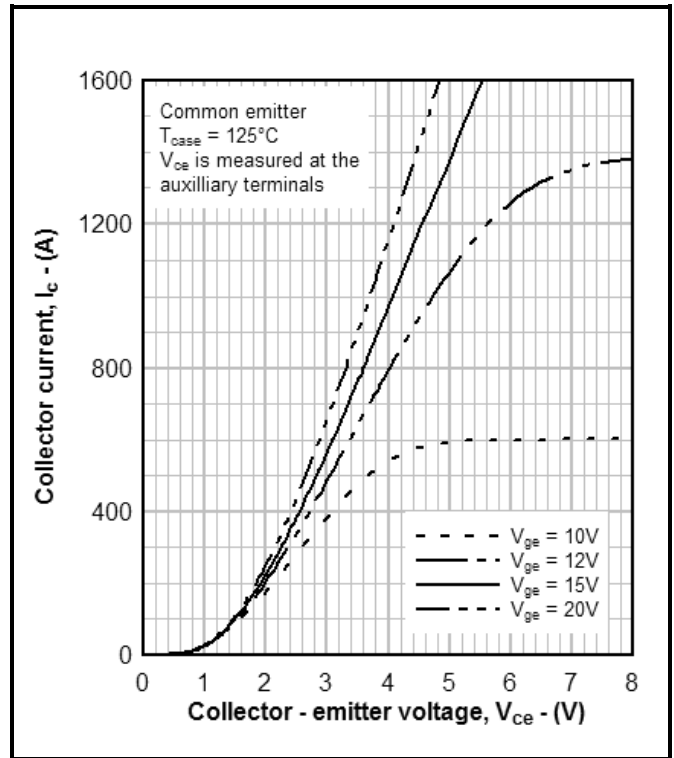


Fig. 4 Typical output characteristics

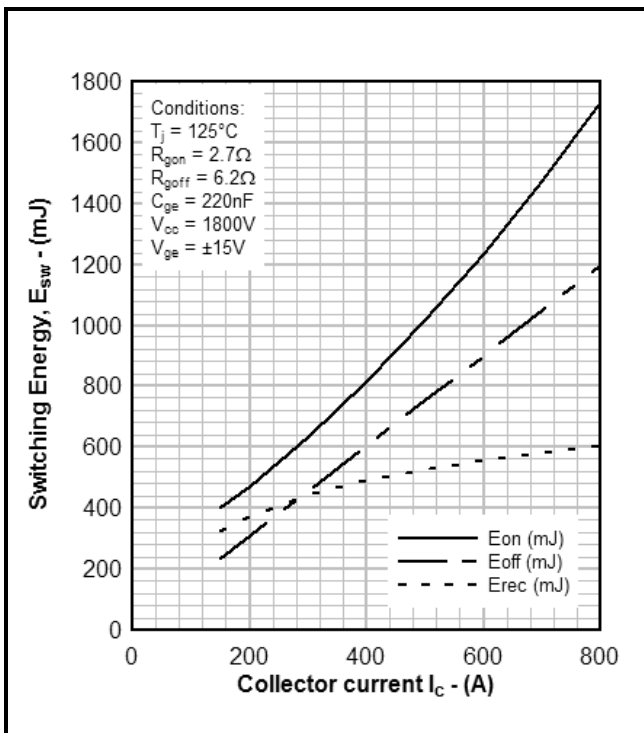


Fig.5 Typical switching energy vs collector current

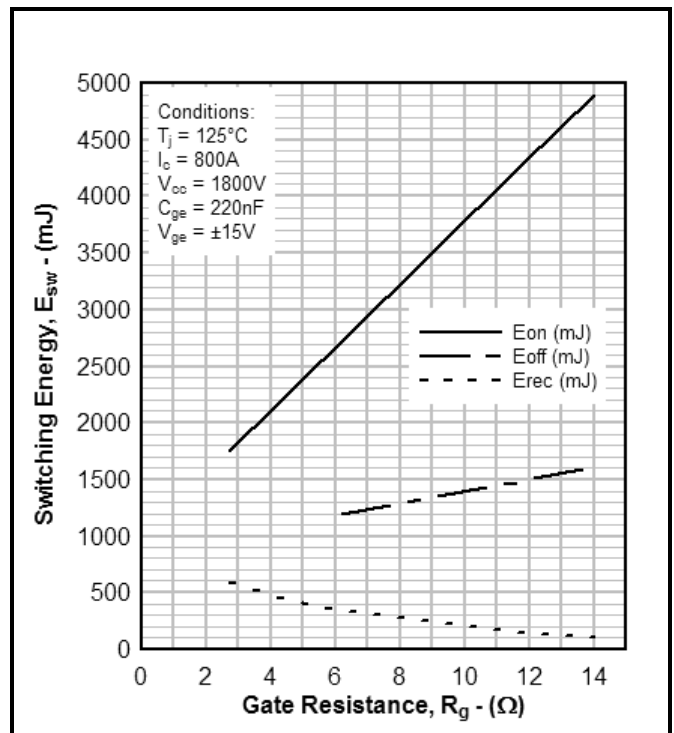


Fig. 6 Typical switching energy vs gate resistance

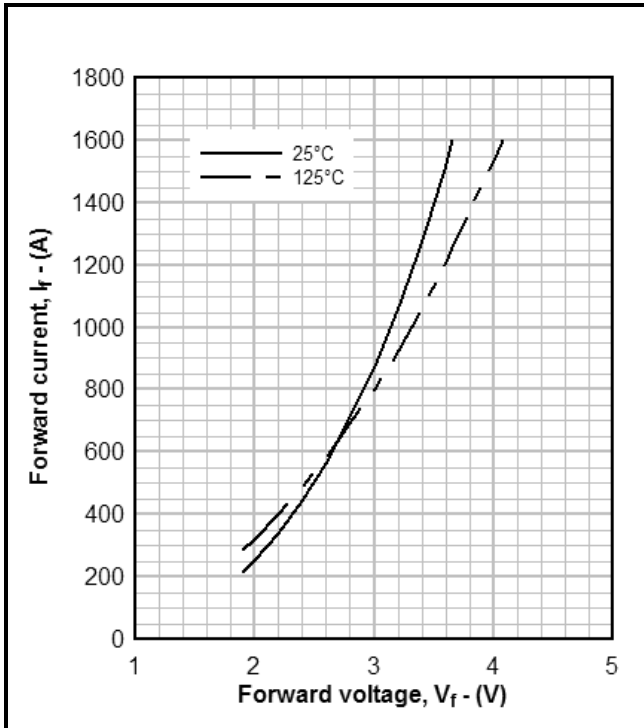


Fig. 7 Diode typical forward characteristics

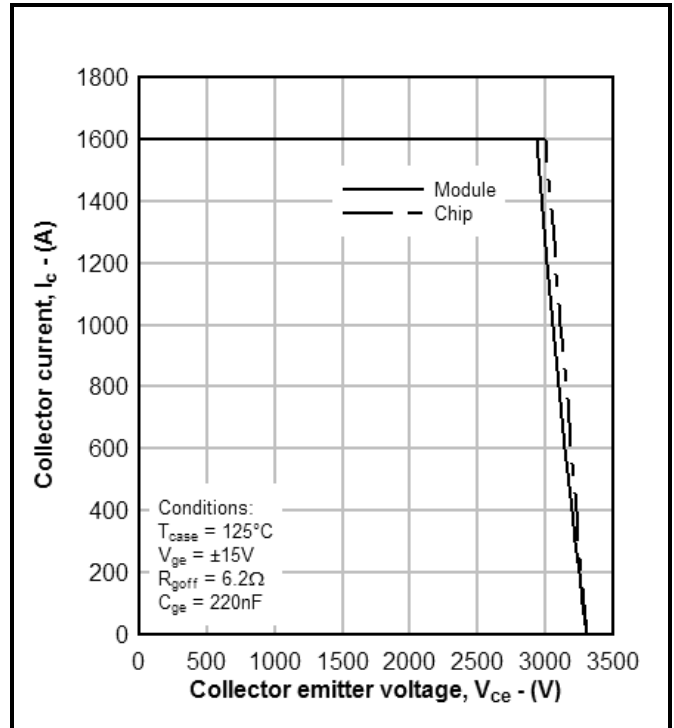


Fig. 8 Reverse bias safe operating area

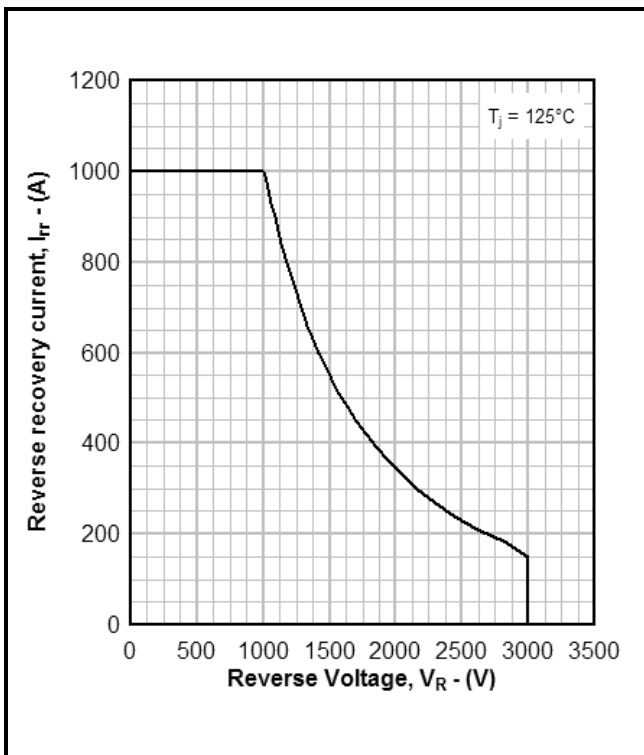


Fig. 9 Diode reverse bias safe operating area

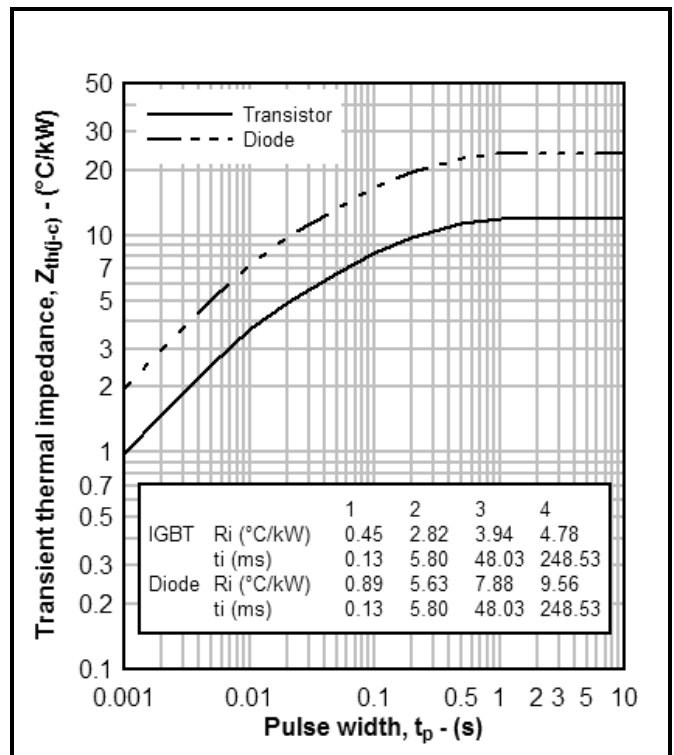
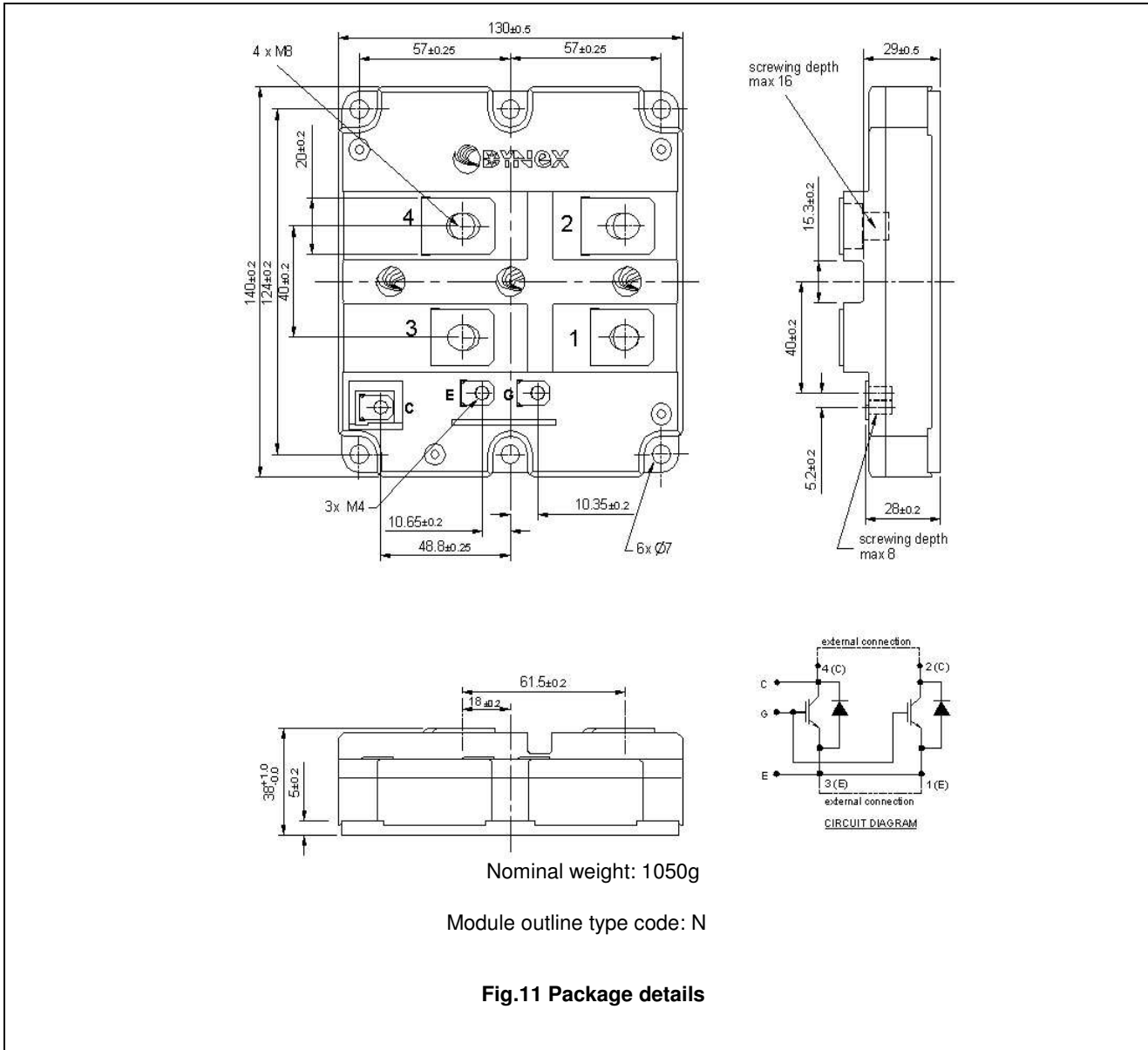


Fig. 10 Transient thermal impedance

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services. All dimensions in mm, unless stated otherwise.
DO NOT SCALE.



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We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group offers high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

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The Power Assembly group has its own proprietary range of extruded aluminium heatsinks which have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or Customer Services.



<http://www.dynexsemi.com>

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